July 2015



FCD5N60 F085

N-Channel SuperFET® MOSFET

600 V, 4.6 A, 1.1 Ω

Features

- 600V, 4.6A, typ. $R_{ds(on)}$ =860m Ω @ V_{GS} =10V
- Ultra Low Gate Charge (Typ. Q_q = 16 nC)
- UIS Capability
- RoHS Compliant
- Qualified to AEC Q101

Applications

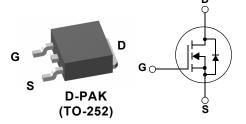
- Automotive On Board Charger
- Automotive DC/DC Converter for HEV



SuperFETTM is Fairchild's proprietary new generation of high voltage MOSFETs utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is suitable for various automotive DC/DC power conversion.





For current package drawing, please refer to the Fairchild website at http://www.fairchildsemi.com/package-drawings/TO/TO252A03.pdf.

MOSFET Maximum Ratings T_{.1} = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-to-Source Voltage		600	V
V_{GS}	Gate-to-Source Voltage		±30	V
	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C = 25°C	4.6	А
ID	Pulsed Drain Current	T _C = 25°C	See Figure 4	A
E _{AS}	Single Pulse Avalanche Energy	(Note 1)	29	mJ
D	Power Dissipation		54	W
P_D	Derate Above 25°C		1.56	W/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 150	οС
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.3	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 2)	83	°C/W

Notes

- 1: Starting $T_J = 25^{\circ}C$, L = 10mH, $I_{AS} = 2.4A$, $V_{DD} = 100V$ during inductor charging and $V_{DD} = 0V$ during time in avalanche.
- 2: R_{0,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,JC} is guaranteed by design, while R_{0,JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCD5N60	FCD5N60_F085	D-PAK(TO-252)	13"	16mm	2500units

Units

Max.

Electrical Characteristics $T_J = 25$ °C unless otherwise noted.

Parameter

Off Characteristics							
B _{VDSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu A, V$	_{'GS} = 0V	600	-	-	V
	Drain-to-Source Leakage Current	V _{DS} =600V,	T _J = 25°C	-	-	1	μА
IDSS Drain-to-Source Leakage Current		$V_{GS} = 0V$	$T_J = 150^{\circ}C \text{ (Note 4)}$	-	-	10	μΑ
lass	Gate-to-Source Leakage Current	$V_{GS} = \pm 30 V$		-	-	±100	nA

Test Conditions

Min.

Тур.

On Characteristics

Symbol

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, I	_D = 250μA	3.0	-	5.0	V
Drain to Source On Begintance	$I_D = 4.6A,$	$T_{J} = 25^{\circ}C$	-	0.86	1.1	Ω	
R _{DS(on)}	R _{DS(on)} Drain to Source On Resistance	V _{GS} = 10V	$T_J = 150^{\circ}C \text{ (Note 4)}$	-	2.5	3.2	Ω

Dynamic Characteristics

C _{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz		-	570	-	pF
Coss	Output Capacitance			-	280	-	pF
C _{rss}	Reverse Transfer Capacitance			-	20	-	pF
R_g	Gate Resistance	f = 1MHz		-	1.9	-	Ω
$Q_{g(ToT)}$	Total Gate Charge	V _{GS} = 0 to 10V	V _{DD} = 480V	-	16	21	nC
Q _{g(th)}	Threshold Gate Charge	$V_{GS} = 0$ to 2V	I _D = 4.6A	-	1.0	-	nC
Q_{gs}	Gate-to-Source Gate Charge		_	-	3.2	-	nC
Q_{gd}	Gate-to-Drain "Miller" Charge			-	7.6	-	nC

Switching Characteristics

t _{on}	Turn-On Time		-	-	84	ns
t _{d(on)}	Turn-On Delay		-	18	-	ns
t _r	Rise Time	$V_{DD} = 300V, I_{D} = 4.6A,$	-	19	-	ns
t _{d(off)}	Turn-Off Delay	V_{DD} = 300V, I_{D} = 4.6A, V_{GS} = 10V, R_{GEN} = 25 Ω	-	48	-	ns
t _f	Fall Time		-	13	-	ns
t _{off}	Turn-Off Time		-	-	178	ns

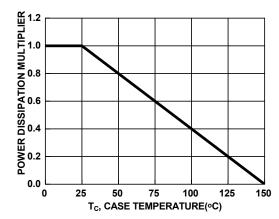
Drain-Source Diode Characteristics

V_{SD}	Source-to-Drain Diode Voltage	I _{SD} = 4.6A, V _{GS} = 0V	-	-	1.25	V
t _{rr}	Reverse-Recovery Time	V _{DD} = 480V, I _F = 4.6A,	-	190	250	ns
Q _{rr}	Reverse-Recovery Charge	dl _{SD} /dt = 100A/μs	-	1.7	2.2	μС

Note

4: The maximum value is specified by design at T_J = 150°C. Product is not tested to this condition in production.

Typical Characteristics



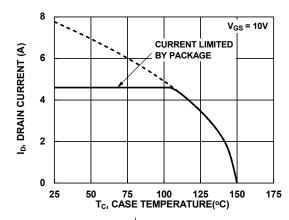


Figure 1. Normalized Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs.

Case Temperature

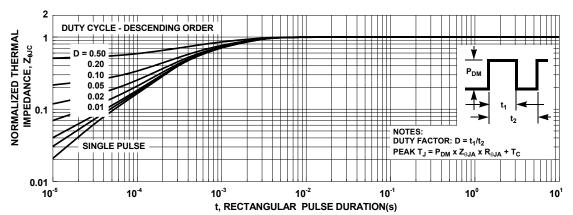


Figure 3. Normalized Maximum Transient Thermal Impedance

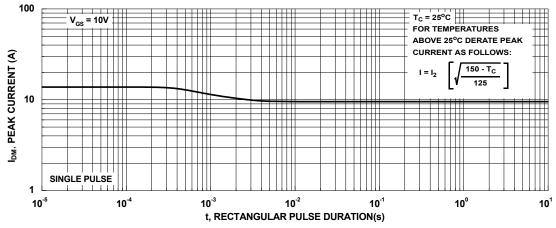
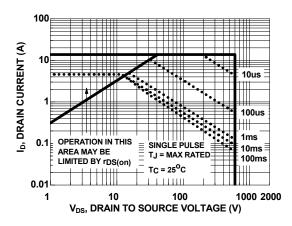


Figure 4. Peak Current Capability

Typical Characteristics



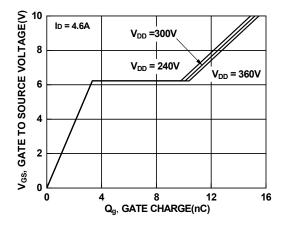
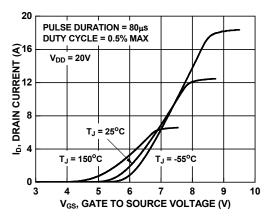


Figure 5. Forward Bias Safe Operating Area

Figure 6. Gate Charge vs. Gate to Source Voltage



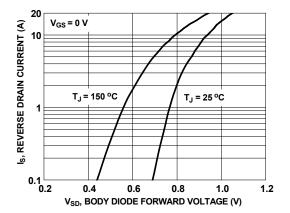
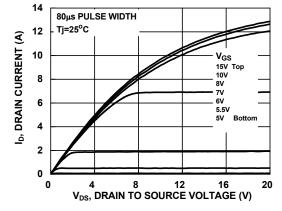


Figure 7. Transfer Characteristics

Figure 8. Forward Diode Characteristics



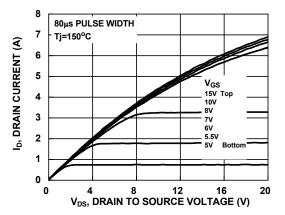


Figure 9. Saturation Characteristics

Figure 10. Saturation Characteristics

Typical Characteristics

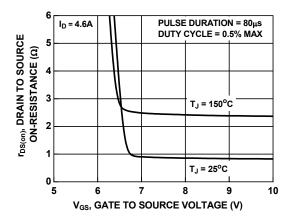


Figure 11. R_{DSON} vs. Gate Voltage

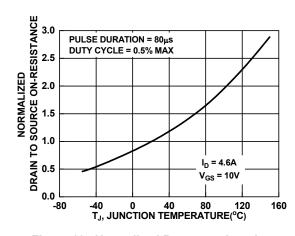


Figure 12. Normalized R_{DSON} vs. Junction Temperature

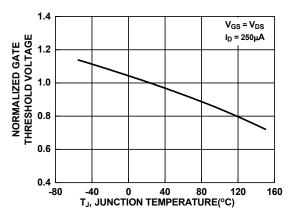


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

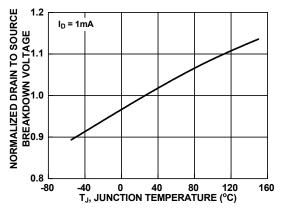


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

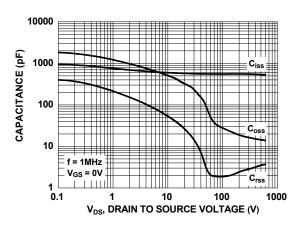


Figure 15. Capacitance vs. Drain to Source Voltage





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